

MA3S132DG, MA3S132EG

Silicon epitaxial planar type

For switching circuits

■ Features

- Short reverse recovery time t_{rr}
- Small terminal capacitance C_t
- Two isolated elements contained in one package, allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---|-----------|-------------|------------------|
| Reverse voltage | V_R | 80 | V |
| Maximum peak reverse voltage | V_{RM} | 80 | V |
| Forward current | Single | I_F | 100 |
| | Double | | 150 |
| Peak forward current | Single | I_{FM} | 225 |
| | Double | | 340 |
| Non-repetitive peak forward surge current * | Single | I_{FSM} | 500 |
| | Double | | 750 |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) *: $t = 1\text{ s}$

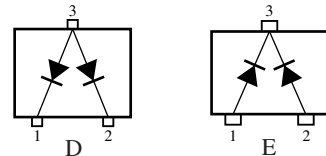
■ Package

- Code
SSMini3-F3
 - Pin Name
MA3S132DG MA3S132EG
- | | |
|--------------|------------|
| 1: Cathode 1 | 1: Anode 1 |
| 2: Cathode 2 | 2: Anode 2 |
| 3: Anode | 3: Cathode |

■ Marking Symbol

MA3S132DG: MO
MA3S132EG: MU

■ Internal Connection



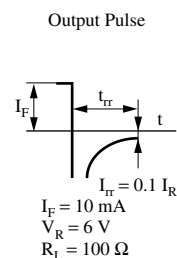
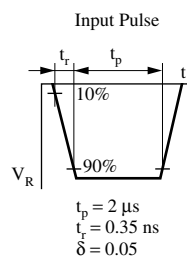
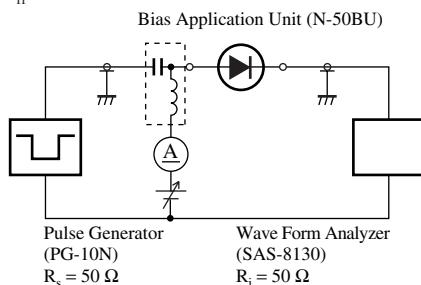
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-------------------------|-----------|---|-----|-----|-----|------|
| Forward voltage | V_F | $I_F = 100\text{ mA}$ | | | 1.2 | V |
| Reverse voltage | V_R | $I_R = 100\ \mu\text{A}$ | 80 | | | V |
| Reverse current | I_R | $V_R = 75\text{ V}$ | | | 100 | nA |
| Terminal capacitance | MA3S132DG | $V_R = 0\text{ V}, f = 1\text{ MHz}$ | | | 15 | pF |
| | MA3S132EG | | | | 2 | |
| Reverse recovery time * | MA3S132DG | $I_F = 10\text{ mA}, V_R = 6\text{ V}$ $I_{rr} = 0.1 I_R, R_L = 100\ \Omega$ | | | 10 | ns |
| | MA3S132EG | | | | 3 | |

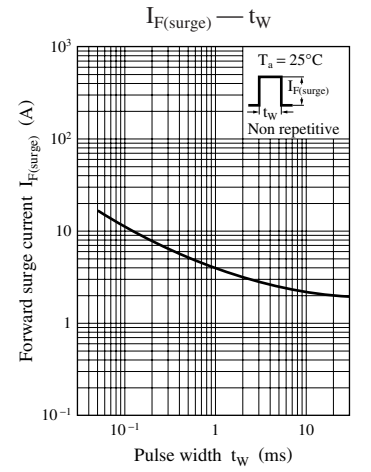
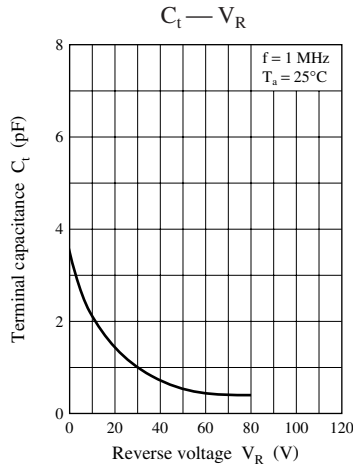
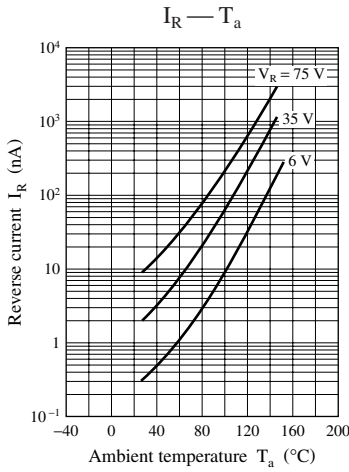
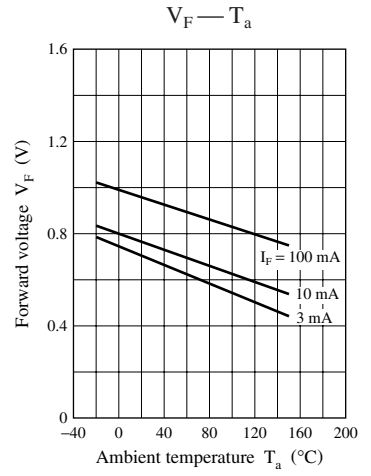
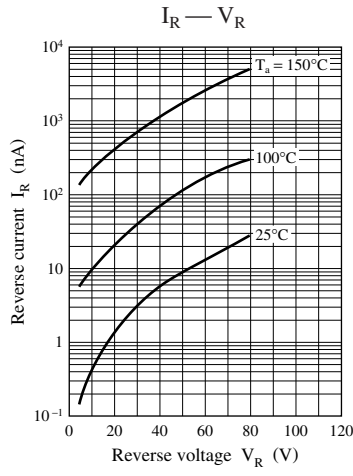
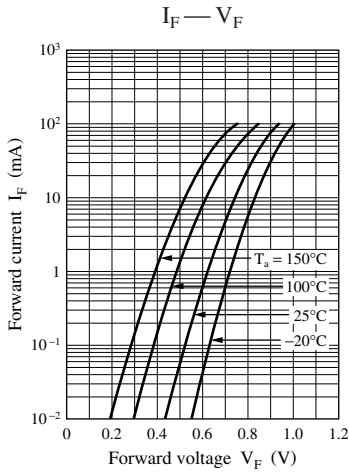
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Absolute frequency of input and output is 100 MHz.

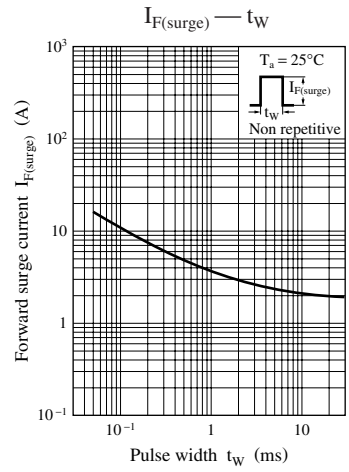
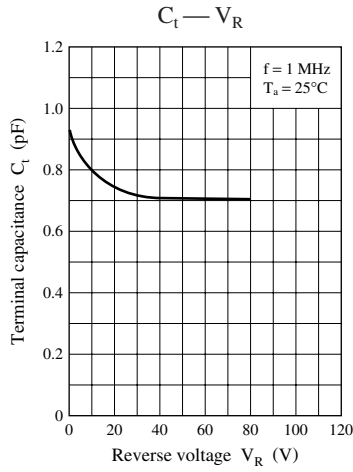
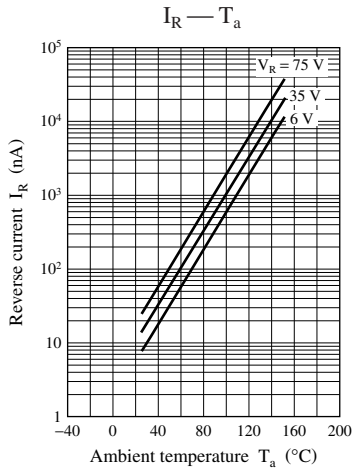
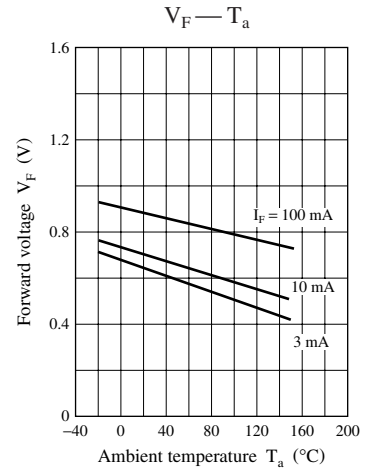
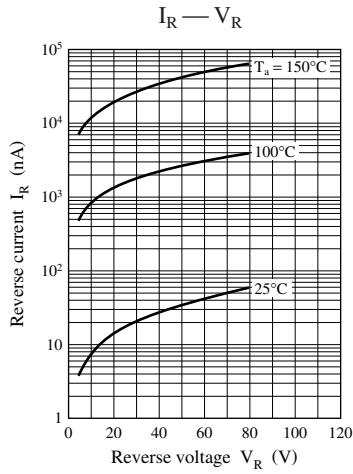
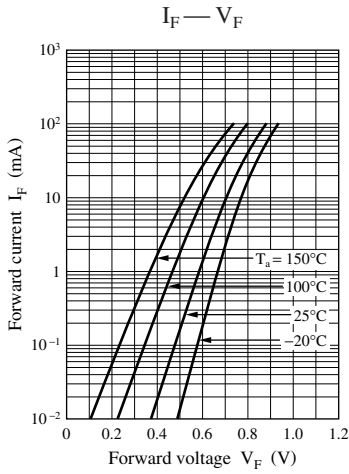
3. *: t_{rr} measurement circuit



Characteristics charts of MA3S132DG

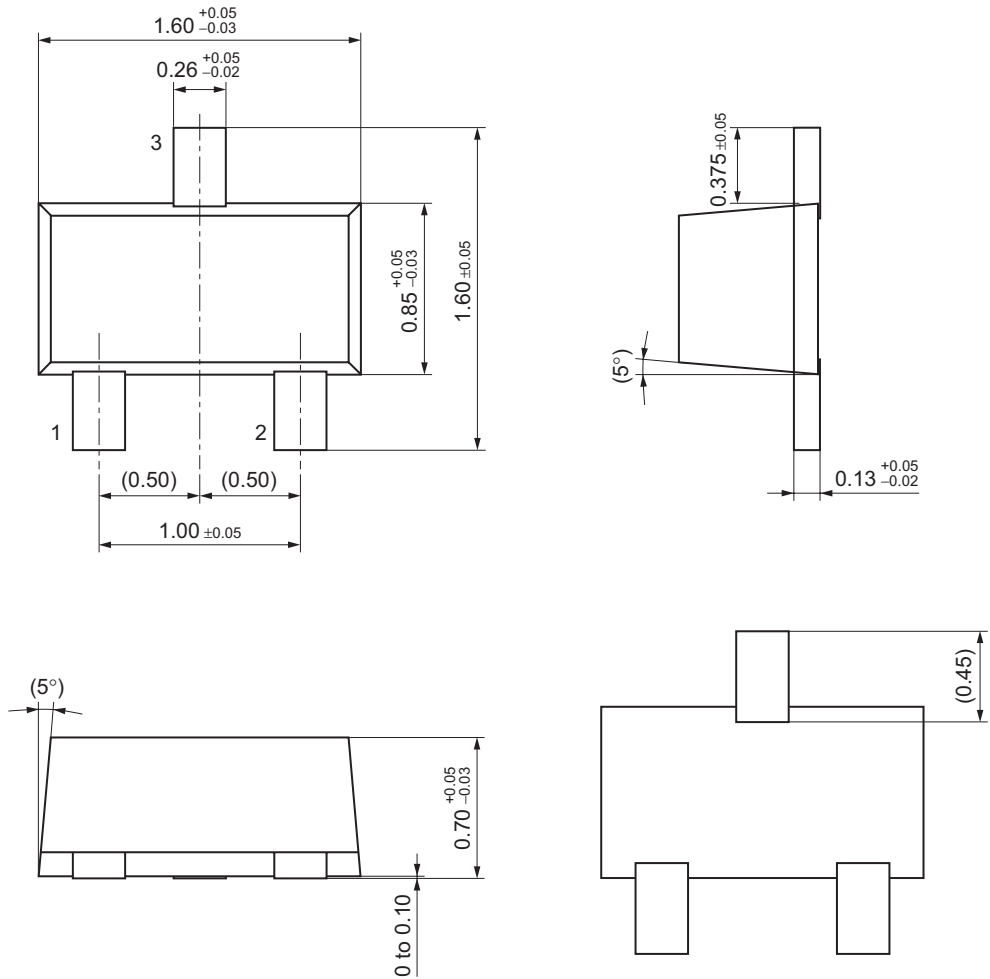


Characteristics charts of MA3S132EG



SSMini3-F3

Unit: mm



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